ICS874003D-02

PRODUCT DISCONTINUATION NOTICE - LAST TIME BUY EXPIRES SEPTEMBER 7, 2016

DATA SHEET

General Description

The ICS874003D-02 is a high performance Differential-to-LVDS Jitter Attenuator. In some PCI Express systems, such as those found in desktop PCs, the PCI Express clocks are generated from a low bandwidth, high phase noise PLL frequency synthesizer. In these systems, a jitter attenuator may be required to attenuate high frequency random and deterministic jitter components from the PLL synthesizer and from the system board. The ICS874003D-02 has a bandwidth of 3MHz. The 3MHz provides an intermediate bandwidth that can easily track triangular spread profiles, while providing good jitter attenuation.

The ICS874003D-02 uses IDT's 3rd Generation FemtoClock[®] PLL technology to achieve the lowest possible phase noise. The device is packaged in a 20-Lead TSSOP package, making it ideal for use in space constrained applications such as PCI Express add-on cards.

Features

- Three differential LVDS output pairs
- One differential clock input
- CLK, nCLK can accept the following differential input levels: LVPECL, LVDS, HCSL
- Input frequency range: 98MHz to 128MHz
- Output frequency range: 98MHz to 320MHz
- VCO range: 490MHz 640MHz
- Cycle-to-Cycle jitter: 30ps (maximum)
- 3MHz PLL loop bandwidth
- 0°C to 70°C ambient operating temperature
- Full 3.3V operating supply
- Lead-free (RoHS 6) packaging
- For drop-in replacement use 874003AG-02

F_SEL[2:0] Function Table

	Inputs		Out	outs
F_SEL2	F_SEL1	F_SEL0	QA[0:1], nQA[0:1]	QB0, nQB0
0	0	0	÷2 (default)	÷2 (default)
1	0	0	÷5	÷2
0	1	0	÷4	÷2
1	1	0	÷2	÷4
0	0	1	÷2	÷5
1	0	1	÷5	÷4
0	1	1	÷4	÷5
1	1	1	÷4	÷4

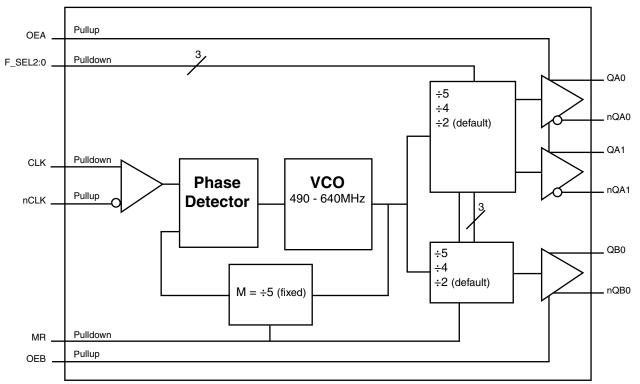
Pin Assignment

QA1 V _{DD0} QA0 nQA0 F_SEL0 V _{DDA} F_SEL1	1 2 3 4 5 6 7 8 9	20 19 18 17 16 15 14 13 12	nQA1 VDDO QB0 nQB0 F_SEL2 OEB GND nCLK
	9 10	12 11	

ICS874003D-02 20-Lead TSSOP 6.5mm x 4.4mm x 0.925mm package body G Package Top View

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Block Diagram



Pin Description and Pin Characteristic Tables

Table 1. Pin Descriptions

Number	Name	Ту	ре	Description
1, 20	QA1, nQA1	Output		Differential output pair. LVDS interface levels.
2, 19	V _{DDO}	Power		Output supply pins.
3, 4	QA0, nQA0	Output		Differential output pair. LVDS interface levels.
5	MR	Input	Pulldown	Active HIGH Master Reset. When logic HIGH, the internal dividers are reset causing the true outputs (Qx) to go low and the inverted outputs (nQx) to go high. When logic LOW, the internal dividers and the outputs are enabled. LVCMOS/LVTTL interface levels.
6, 9, 16	F_SEL0, F_SEL1, F_SEL2	Input	Pulldown	Frequency select pin for QAx, nQAx and QB0, nQB0 outputs. LVCMOS/LVTTL interface levels.
7	nc	Unused		No connect.
8	V _{DDA}	Power		Analog supply pin.
10	V _{DD}	Power		Core supply pin.
11	OEA	Input	Pullup	Output enable pin for QAx pins. When HIGH, the QAx, nQAx outputs are active. When LOW, the QAx, nQAx outputs are in a high impedance state. LVCMOS/LVTTL interface levels.
12	CLK	Input	Pulldown	Non-inverting differential clock input.
13	nCLK	Input	Pullup	Inverting differential clock input.
14	GND	Power		Power supply ground.
15	OEB	Input	Pullup	Output enable pin for QB0 pins. When HIGH, the QB0, nQB0 outputs are active. When LOW, the QB0, nQB0 outputs are in a high impedance state. LVCMOS/LVTTL interface levels.
17, 18	nQB0, QB0	Output		Differential output pair. LVDS interface levels.

NOTE: Pullup and Pulldown refer to internal input resistors. See Table 2, Pin Characteristics, for typical values.

Table 2. Pin Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C _{IN}	Input Capacitance			4		pF
R _{PULLUP}	Input Pullup Resistor			51		kΩ
R _{PULLDOWN}	Input Pulldown Resistor			51		kΩ

Function Table

Table 3. Output Enable Function Table

Inputs		Outputs		
OEA	OEB	QA[0:1], nQA[0:1]	QB0, nQB0	
0	0	Hi-Impedance	Hi-Impedance	
1	1	Enabled	Enabled	

Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of the product at these conditions or any conditions beyond those listed in the *DC Characteristics or AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, V _{DD}	4.6V
Inputs, V _I	-0.5V to V _{DD} + 0.5V
Outputs, I _O	
Continuous Current	10mA
Surge Current	15mA
Package Thermal Impedance, θ_{JA}	86.7°C/W (0 mps)
Storage Temperature, T _{STG}	-65°C to 150°C

DC Electrical Characteristics

Table 4A. LVDS Power Supply DC Characteristics, V_{DD} = V_{DDO} = 3.3V \pm 5%, T_{A} = 0°C to 70°C

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{DD}	Core Supply Voltage		3.135	3.3	3.465	V
V _{DDA}	Analog Supply Voltage		V _{DD} – 0.15	3.3	V _{DD}	V
V _{DDO}	Output Supply Voltage		3.135	3.3	3.465	V
I _{DD}	Power Supply Current				80	mA
I _{DDA}	Analog Supply Current				15	mA
I _{DDO}	Output Supply Current				75	mA

Table 4B. LVCMOS/LVTTL DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = 0^{\circ}C$ to $70^{\circ}C$

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
V _{IH}	Input High Vo	Itage		2		V _{DD} + 0.3	V
V _{IL}	Input Low Vol	tage		-0.3		0.8	V
	Input High	OEA, OEB	$V_{DD} = V_{IN} = 3.465V$			5	μA
Input High Current		MR, F_SEL[2:0]	$V_{DD} = V_{IN} = 3.465V$			150	μA
	Input Low	OEA, OEB	V _{DD} = 3.465V, V _{IN} = 0V	-150			μA
	Input Low Current	MR, F_SEL[2:0]	V _{DD} = 3.465V, V _{IN} = 0V	-5			μA

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
1	Input High	CLK	V _{DD} = V _{IN} = 3.465V			150	μA
Current	nCLK	V _{DD} = V _{IN} = 3.465V			5	μA	
	Input Low	CLK	V _{DD} = 3.465V, V _{IN} = 0V	-5			μA
LIL Current	Current	nCLK	V _{DD} = 3.465V, V _{IN} = 0V	-150			μA
V _{PP}	Peak-to-Peak NOTE 1	< Voltage;		0.15		1.3	V
V _{CMR}	Common Mo Voltage; NOT	•		GND + 0.5		V _{DD} – 0.85	V

Table 4C. Differential DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = 0^{\circ}C$ to $70^{\circ}C$

NOTE 1: V_{IL} should not be less than -0.3V.

NOTE 2: Common mode input voltage is defined as VIH.

Table 4D. LVDS DC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = 0^{\circ}C$ to $70^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
V _{OD}	Differential Output Voltage		275	375	485	mV
ΔV_{OD}	V _{OD} Magnitude Change				50	mV
V _{OS}	Offset Voltage		1.2	1.35	1.5	V
ΔV_{OS}	V _{OS} Magnitude Change				50	mV

Table 5. AC Characteristics, $V_{DD} = V_{DDO} = 3.3V \pm 5\%$, $T_A = 0^{\circ}C$ to $70^{\circ}C$

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
fout	Output Frequency		98		320	MHz
<i>t</i> jit(cc)	Cycle-to-Cycle Jitter; NOTE 1				30	ps
<i>tsk</i> (o)	Output Skew; NOTE 2, 3				185	ps
<i>tsk</i> (b)	Bank Skew; NOTE 1, 4	Bank A			65	ps
t _R / t _F	Output Rise/Fall Time	20% to 80%	250		700	ps
odc	Output Duty Cycle		47		53	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

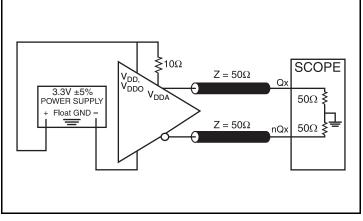
NOTE 1: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at the differential crosspoints.

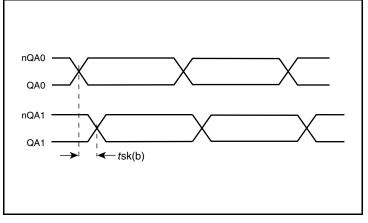
NOTE 3: These parameters are guaranteed by characterization. Not tested in production.

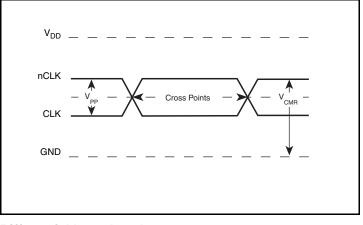
NOTE 4: Defined as skew within a bank of outputs at the same voltage and with equal load conditions.

Parameter Measurement Information

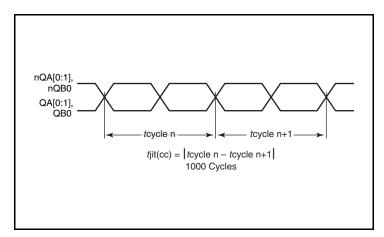


3.3V LVDS Output Load Test Circuit

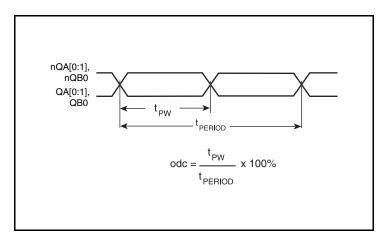




Differential Input Level

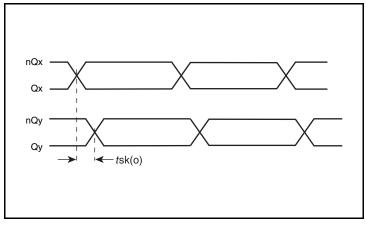


Cycle-to-Cycle Jitter



Output Duty Cycle/Pulse Width/Period

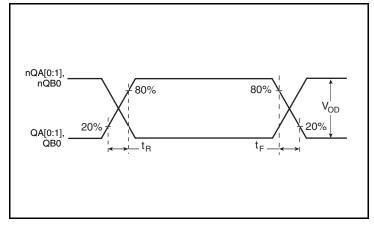
Bank Skew

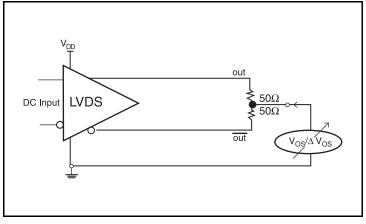


Output Skew

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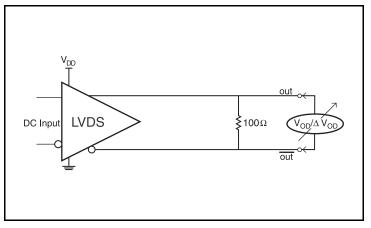
Parameter Measurement Information, continued





Offset Voltage Setup





Differential Output Voltage Setup

Applications Information

Wiring the Differential Input to Accept Single-Ended Levels

Figure 1 shows how a differential input can be wired to accept single ended levels. The reference voltage $V_1 = V_{CC}/2$ is generated by the bias resistors R1 and R2. The bypass capacitor (C1) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of R1 and R2 might need to be adjusted to position the V₁ in the center of the input voltage swing. For example, if the input clock swing is 2.5V and V_{CC} = 3.3V, R1 and R2 value should be adjusted to set V₁ at 1.25V. The values below are for when both the single ended swing and V_{CC} are at the same voltage. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First, R3 and R4 in parallel should equal the transmission line impedance. For most 50 Ω applications, R3 and R4 can be 100 Ω . The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver. When using single-ended signaling, the noise rejection benefits of differential signaling are reduced. Even though the differential input can handle full rail LVCMOS signaling, it is recommended that the amplitude be reduced. The datasheet specifies a lower differential amplitude, however this only applies to differential signals. For single-ended applications, the swing can be larger, however V_{IL} cannot be less than -0.3V and V_{IH} cannot be more than V_{CC} + 0.3V. Though some of the recommended components might not be used, the pads should be placed in the layout. They can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a differential signal.

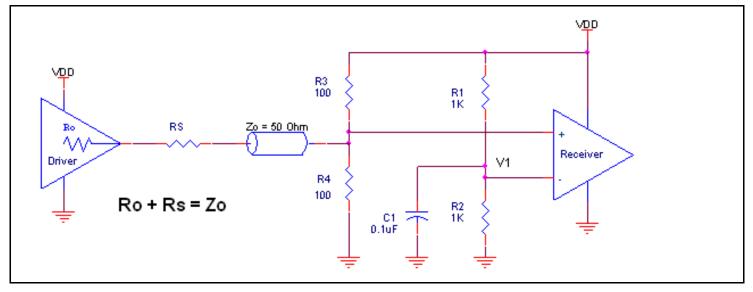


Figure 1. Recommended Schematic for Wiring a Differential Input to Accept Single-ended Levels

Differential Clock Input Interface

The CLK /nCLK accepts LVDS, LVPECL, HCSL and other differential signals. The differential signal must meet the V_{PP} and V_{CMR} input requirements. *Figures 2A* to *2D* show interface examples for the CLK/nCLK input driven by the most common driver types. The input

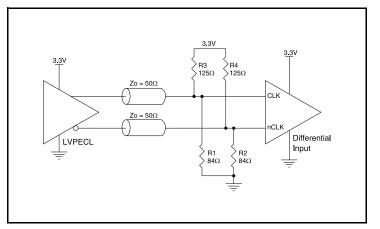


Figure 2A. CLK/nCLK Input Driven by a 3.3V LVPECL Driver

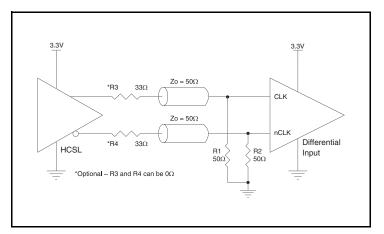
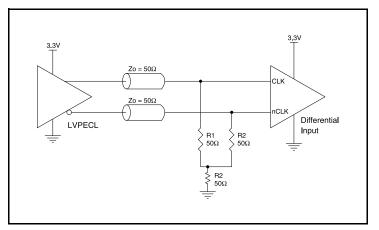


Figure 2C. CLK/nCLK Input Driven by a 3.3V HCSL Driver

interfaces suggested here are examples only. Please consult with the vendor of the driver component to confirm the driver termination requirements.





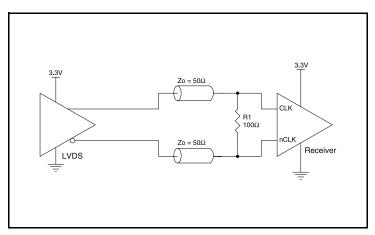


Figure 2D. CLK/nCLK Input Driven by a 3.3V LVDS Driver

Recommendations for Unused Input and Output Pins

Inputs:

LVCMOS Control Pins

All control pins have internal pullup or pulldown resistors; additional resistance is not required but can be added for additional protection. A $1k\Omega$ resistor can be used.

Outputs:

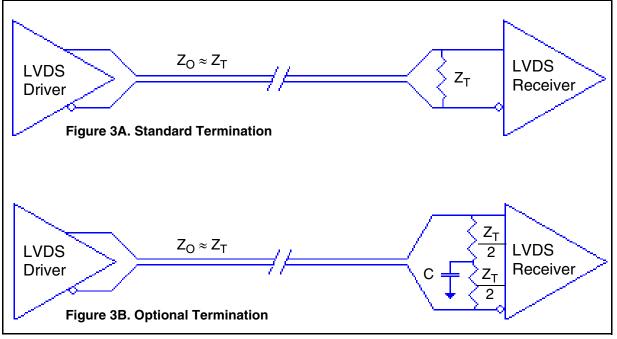
LVDS Outputs

All unused LVDS output pairs can be either left floating or terminated with 100Ω across. If they are left floating, there should be no trace attached.

LVDS Driver Termination

For a general LVDS interface, the recommended value for the termination impedance (Z_T) is between 90 Ω and 132 Ω . The actual value should be selected to match the differential impedance (Z₀) of your transmission line. A typical point-to-point LVDS design uses a 100 Ω parallel resistor at the receiver and a 100 Ω differential transmission-line environment. In order to avoid any transmission-line reflection issues, the components should be surface mounted and must be placed as close to the receiver as possible. IDT offers a full line of LVDS compliant devices with two types of output structures: current source and voltage source. The

standard termination schematic as shown in *Figure 3A* can be used with either type of output structure. *Figure 3B*, which can also be used with both output types, is an optional termination with center tap capacitance to help filter common mode noise. The capacitor value should be approximately 50pF. If using a non-standard termination, it is recommended to contact IDT and confirm if the output structure is current source or voltage source type. In addition, since these outputs are LVDS compatible, the input receiver's amplitude and common-mode input range should be verified for compatibility with the output.



LVDS Termination

Schematic Layout

Figure 4 shows an example of ICS874003D-02 application schematic. This example focuses on functional connections and is not configuration specific. In this example, the device is operated at $V_{DD} = V_{DDO} = 3.3V$. Refer to the pin description and functional tables in the datasheet to ensure the logic control inputs are properly set. For the LVDS output drivers, two termination examples are shown in the schematic.

As with any high speed analog circuitry, the power supply pins are vulnerable to random noise. To achieve optimum jitter performance, power supply isolation is required. The ICS874003D-02 provides separate V_{DD} , V_{DDA} and V_{DDO} power supplies to isolate any high switching noise from coupling into the internal oscillator. In order to achieve the best possible filtering, it is highly recommended that the 0.1uF capacitors on the device side of the ferrite beads be placed on the device side of the PCB as close to the power pins as

possible. This is represented by the placement of these capacitors in the schematic. If space is limited, the ferrite beads, 10μ F and 0.1μ F capacitor connected to the board supplies can be placed on the opposite side of the PCB. If space permits, place all filter components on the device side of the board.

Power supply filter recommendations are a general guideline to be used for reducing external noise from coupling into the devices. The filter performance is designed for a wide range of noise frequencies. This low-pass filter starts to attenuate noise at approximately 10 kHz. If a specific frequency noise component is known, such as switching power supplies frequencies, it is recommended that component values be adjusted and if required, additional filtering be added. Additionally, good general design practices for power plane voltage stability suggests adding bulk capacitance in the local area of all devices.

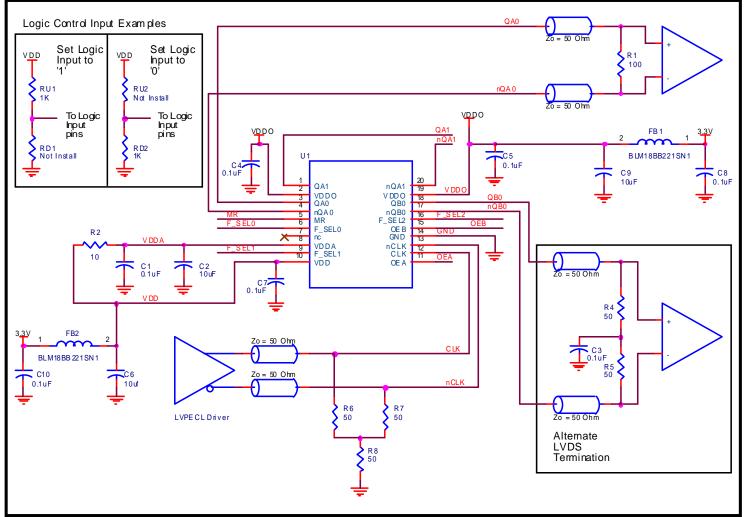


Figure 4. ICS874003D-02 Schematic Layout

Power Considerations

This section provides information on power dissipation and junction temperature for the ICS874003D-02. Equations and example calculations are also provided.

1. Power Dissipation.

The total power dissipation for the ICS74003D-02 is the sum of the core power plus the analog power plus the power dissipated due to the load. The following is the power dissipation for $V_{DD} = 3.3V + 5\% = 3.465V$, which gives worst case results.

- Power (core)_{MAX} = V_{DD_MAX} * (I_{DD_MAX} + I_{DDA_MAX}) = 3.465V * (80mA + 15mA) = 329.175mW
- Power (outputs)_{MAX} = V_{DDO MAX} * I_{DDO MAX} = 3.465V * 75mA = 259.87mW

Total Power_MAX = 329.175mW + 259.87mW = 589.045mW

•

2. Junction Temperature.

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: Tj = θ_{JA} * Pd_total + T_A

Tj = Junction Temperature

 θ_{JA} = Junction-to-Ambient Thermal Resistance

Pd_total = Total Device Power Dissipation (example calculation is in section 1 above)

T_A = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance θ_{JA} must be used. Assuming no air flow and a multi-layer board, the appropriate value is 86.7°C/W per Table 6 below.

Therefore, Tj for an ambient temperature of 70°C with all outputs switching is:

70°C + 0.589W * 86.7°C/W = 121.1°C. This is below the limit of 125°C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

Table 6. Thermal Resistance θ_{JA} for 20-Lead TSSOP, Forced Convection

θ_{JA} by Velocity					
Meters per Second	0	1	2.5		
Multi-Layer PCB, JEDEC Standard Test Boards	86.7°C/W	82.4°C/W	80.2°C/W		

Reliability Information

Table 7. θ_{JA} vs. Air Flow Table for a 20-Lead TSSOP

θ _{JA} by Velocity					
Meters per Second	0	1	2.5		
Multi-Layer PCB, JEDEC Standard Test Boards	86.7°C/W	82.4°C/W	80.2°C/W		

Transistor Count

The transistor count for ICS874003D-02 is: 1408

Package Outline and Package Dimensions

Package Outline - G Suffix for 20-Lead TSSOP

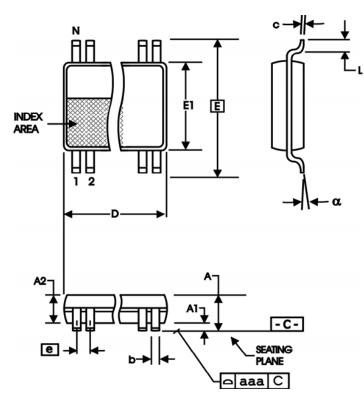


Table 8. Package Dimensions

All Dimensions in Millimeters					
Symbol	Minimum	Maximum			
N	20				
Α		1.20			
A1	0.05	0.15			
A2	0.80	1.05			
b	0.19	0.30			
С	0.09	0.20			
D	6.40	6.60			
E	6.40 Basic				
E1	4.30	4.50			
е	0.65 Basic				
L	0.45	0.75			
α	0°	8°			
aaa		0.10			

Reference Document: JEDEC Publication 95, MO-153

Ordering Information

Table 9. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
874003DG-02LF	ICS74003D02L	"Lead-Free" 20-Lead TSSOP	Tube	0°C to 70°C
874003DG-02LFT	ICS74003D02L	"Lead-Free" 20-Lead TSSOP	Tape & Reel	0°C to 70°C

Revision History

3/11/16 Product Discontinuation Notice - Last time buy expires September 7, 2016. PDN N-16-02



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